



N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	100V
I_D	27A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	29m
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	47m
100% EAS Tested	
100% V_{DS} Tested	

YJD27G10A



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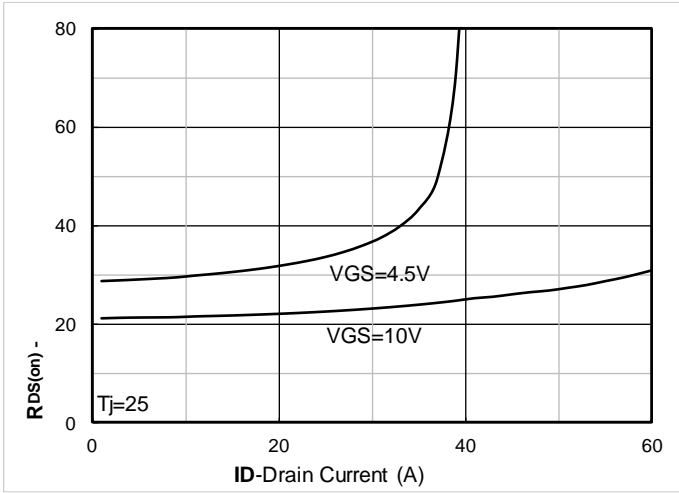


Figure 7. RDS(on) VS Drain Current

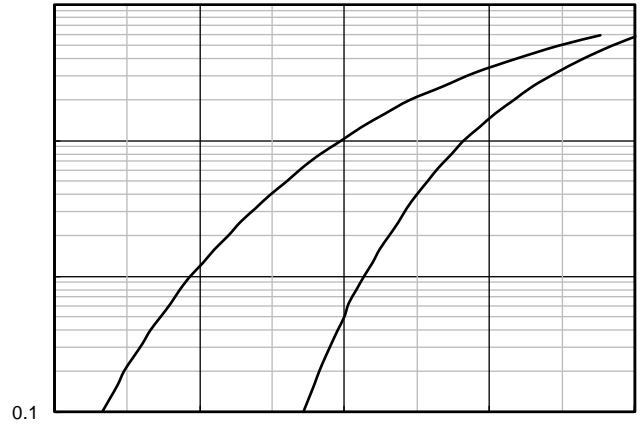


Figure 8. Forward characteristics of reverse diode

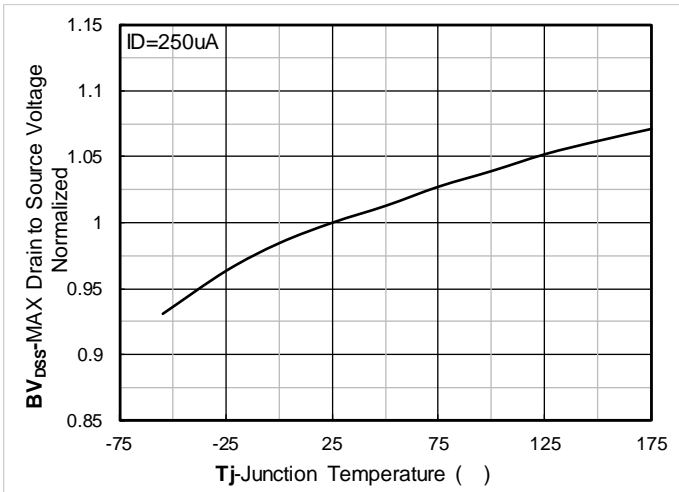


Figure 9. Normalized breakdown voltage

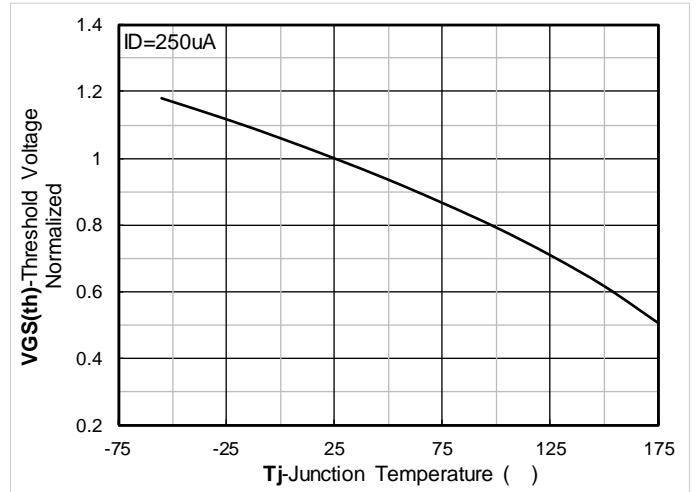


Figure 10. Normalized threshold voltage



Figure B. Gate Charge Test Circuit & Waveform



Figure C. Resistive Switching Test Circuit & Waveform

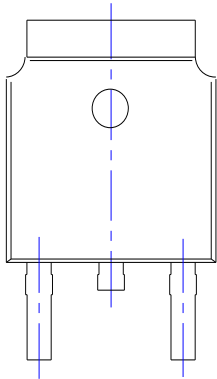


Figure D. Diode Recovery Test Circuit & Waveform



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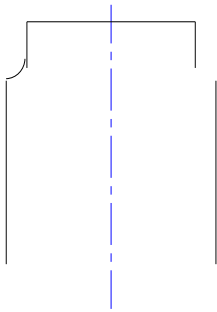
TO-252-B Package information



TOP VIEW



SIDE VIEW



BOTTOM VIEW

SUGGESTED SOLDER PAD LAYOUT

SYMBOL	DIMENSIONS				
	INCHES				
	MIN.	NOM.			
A1	0.000				
A2	0.087	0.091			
A3	0.035	0.039			
b	0.026	0.030			
c	0.018	0.020			
D	0.256	0.260			
D1					
D2	0.181	0.189			
E	0.390	0.398			
E1	0.236	0.240			

NOTE:

- 1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
- 2. TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
- 3. THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.

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